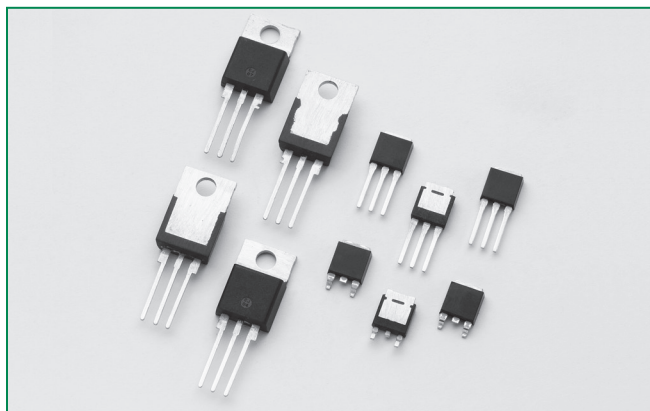




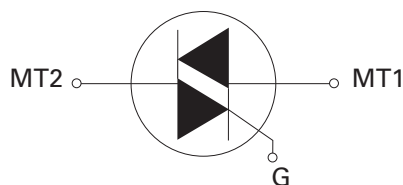
Agency Approval

Agency	Agency File Number
	L Package : E71639

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	400 to 1000	V
$I_{GT(Q1)}$	3 to 25	mA

Schematic Symbol



Description

4 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 55 A
- Electrically isolated “L-Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point of sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Typical applications are AC solid-state switches, power tools, home/brown goods and white goods appliances.

Sensitive gate Triacs can be directly driven by microprocessor or popular opto-couplers/isolators.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Sensitive Triacs (4 Quadrants)

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	Lxx04Ly / Lxx04Dy	T _C = 85°C	4	A
		Lxx04Ry / Lxx04Vy	T _C = 75°C		
I _{TSM}	Non repetitive surge peak on-state current (full cycle, T _J initial = 25°C)	f = 50 Hz	t = 20 ms	33	A
		f = 60 Hz	t = 16.7 ms	40	
I ² t	I ² t Value for fusing	t _p = 8.3 ms		6.6	A ² s
di/dt	Critical rate of rise of on-state current (I _G = 50mA with ≤ 0.1μs rise time)	f = 120 Hz	T _J = 110°C	50	A/μs
I _{GTM}	Peak gate trigger current	t _p ≤ 10 μs	T _J = 110°C	1.2	A
P _{G(AV)}	Average gate power dissipation		T _J = 110°C	0.3	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 110	°C

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard Triacs

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx04Ly / Qxx04Dy	$T_c = 95^\circ\text{C}$	4	A
		Qxx04Ry / Qxx04Vy	$T_c = 85^\circ\text{C}$		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	f = 50 Hz	t = 20 ms	46	A
		f = 60 Hz	t = 16.7 ms	55	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms		12.5	A^2s
di/dt	Critical rate of rise of on-state current ($I_G = 50\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz	$T_J = 125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GTM}	Peak gate trigger current	$t_p \leq 10\mu\text{s};$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	1.2	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.3	W
T_{stg}	Storage temperature range			-40 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Sensitive Triac (4 Quadrants)

Symbol	Test Conditions	Quadrant		Lxx04x3	Lxx04x5	Lxx04x6	Lxx04x8	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\Omega$	I – II – III	MAX.	3	5	5	10	mA
		IV		3	5	10	20	
V_{GT}		ALL	MAX.	1.3				V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{k}\Omega$ $T_J = 110^\circ\text{C}$	ALL	MIN.	0.2				V
I_H	$I_T = 100\text{mA}$		MAX.	5	10	10	15	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	400V	TYP.	25	25	30	35	$\text{V}/\mu\text{s}$
		600V		15	15	20	25	
(dv/dt)c	(di/dt)c = 2.16 A/ms $T_J = 110^\circ\text{C}$		TYP.	0.5	1	1	1	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 5.6\text{A(pk)}$		TYP.	2.8	3.0	3.0	3.2	μs

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

Symbol	Test Conditions	Quadrant		Qxx04x3	Qxx04x4	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60\Omega$	I – II – III	MAX.	10	25	mA
		IV	TYP.	25	50	
V_{GT}		I – II – III	MAX.	1.3	1.3	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{k}\Omega$ $T_J = 125^\circ\text{C}$	ALL	MIN.	0.2	0.2	V
I_H	$I_T = 200\text{mA}$		MAX.	20	30	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	40	75	$\text{V}/\mu\text{s}$
		600V		30	50	
		800V			40	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V			50	
(dv/dt)c	(di/dt)c = 2.16 A/ms $T_J = 125^\circ\text{C}$		TYP.	2	2	$\text{V}/\mu\text{s}$
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 5.6\text{A(pk)}$		TYP.	2.5	3.0	μs

Note: xx = voltage, x = package

Static Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions					Value	Unit
V_{TM}	$I_{TM} = 5.6\text{A}$ $t_p = 380\text{ }\mu\text{s}$		MAX.			1.60	V
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$	MAX.	Lxx04xy	$T_J = 25^\circ\text{C}$	400-600V	5	μA
				$T_J = 110^\circ\text{C}$	400-600V	200	μA
			Qxx04xy	$T_J = 25^\circ\text{C}$	400-1000V	10	μA
				$T_J = 125^\circ\text{C}$	400-800V	2	mA
				$T_J = 100^\circ\text{C}$	1000V	3	

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	L/Qxx04Dy	3.5	$^\circ\text{C/W}$
		L/Qxx04Ly	3.6	
		L/Qxx04Ry	3.6	
		L/Qxx04Vy	6.0	
$R_{\theta(J-A)}$	Junction to ambient	L/Qxx04Ly	50	$^\circ\text{C/W}$
		L/Qxx04Ry	45	
		L/Qxx04Vy	70	

Note: xx = voltage, x = package, y = sensitivity

Figure 1: Definition of Quadrants

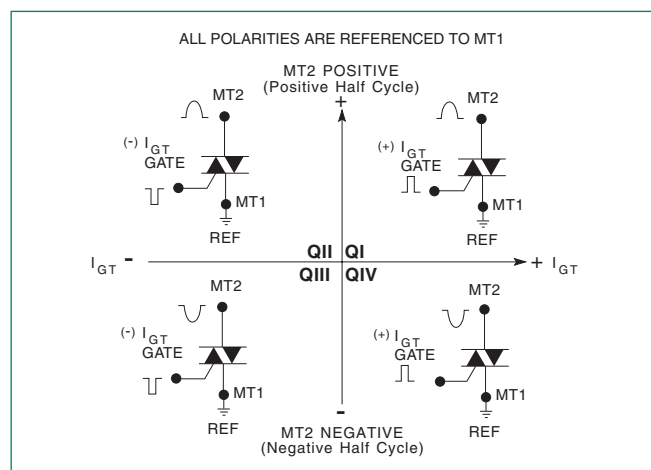


Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature

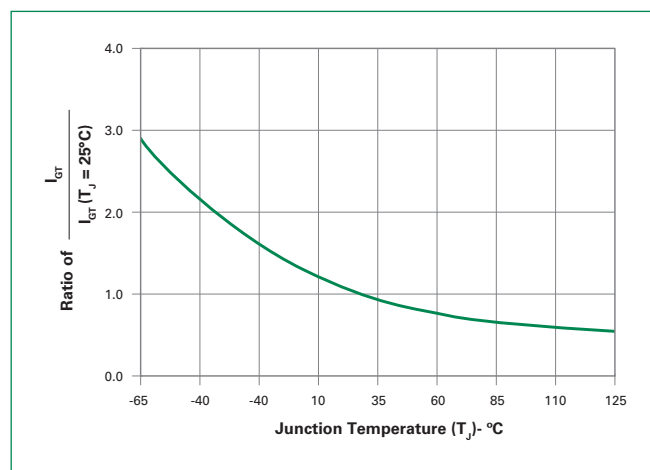


Figure 3: Normalized DC Holding Current vs. Junction Temperature

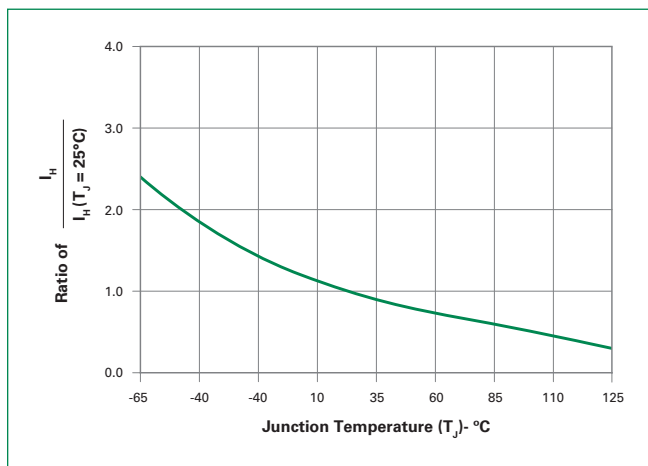


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature

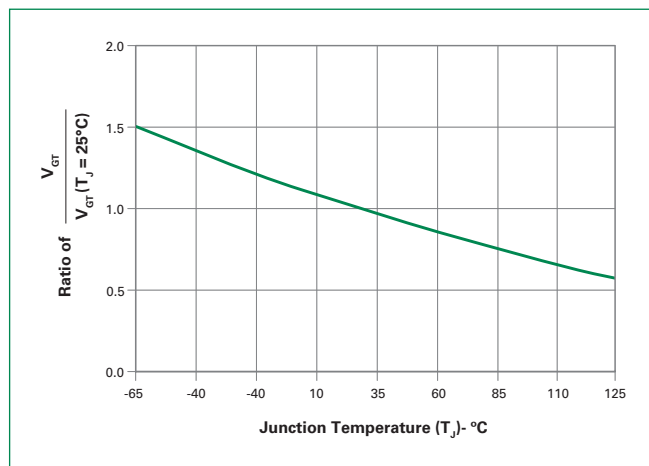


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

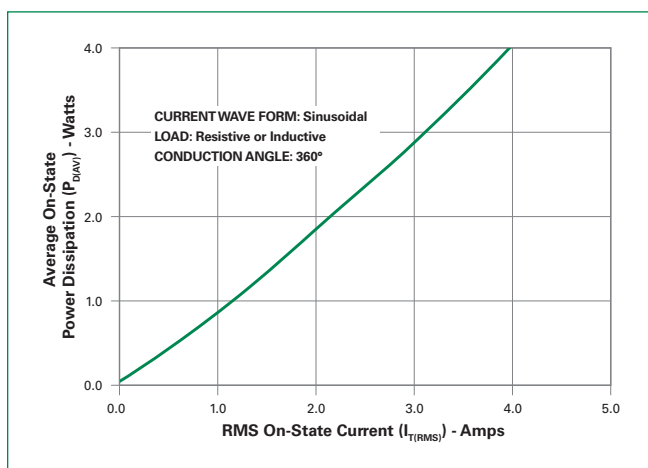


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

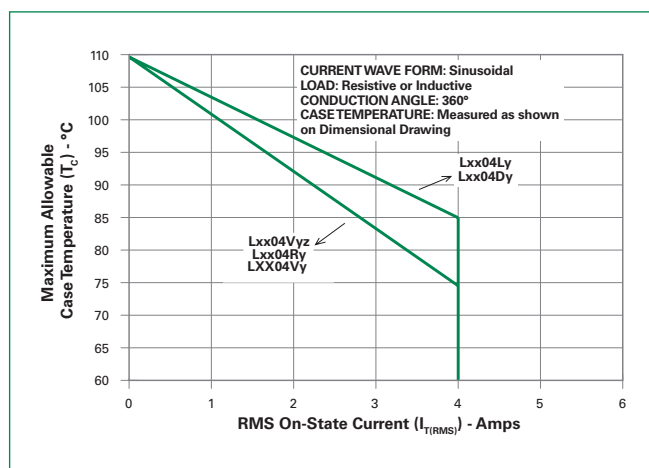


Figure 7: Maximum Allowable Case Temperature vs. On-State Current

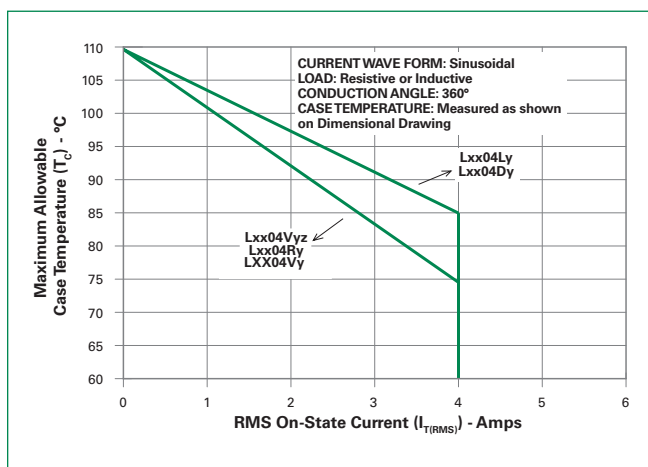
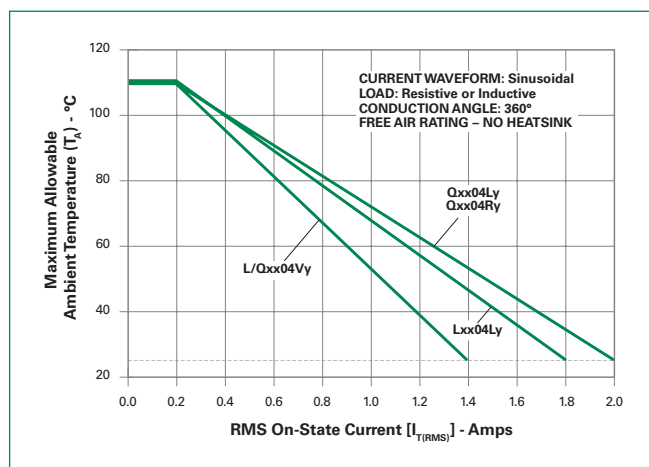


Figure 8: Maximum Allowable Ambient Temperature vs. On-State Current



Note: xx = voltage, y = sensitivity

Figure 9: On-State Current vs. On-State Voltage (Typical)

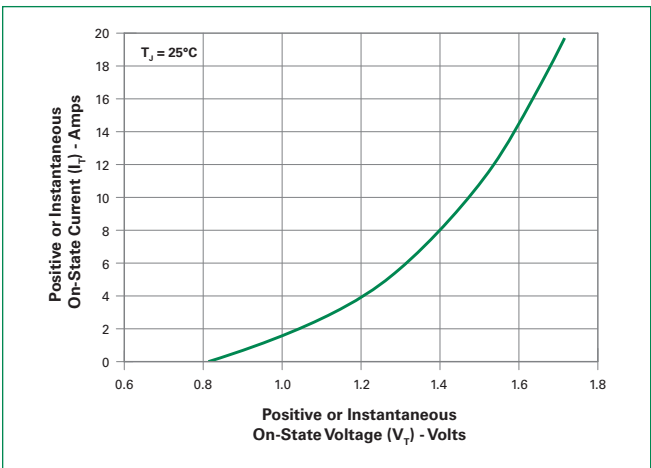
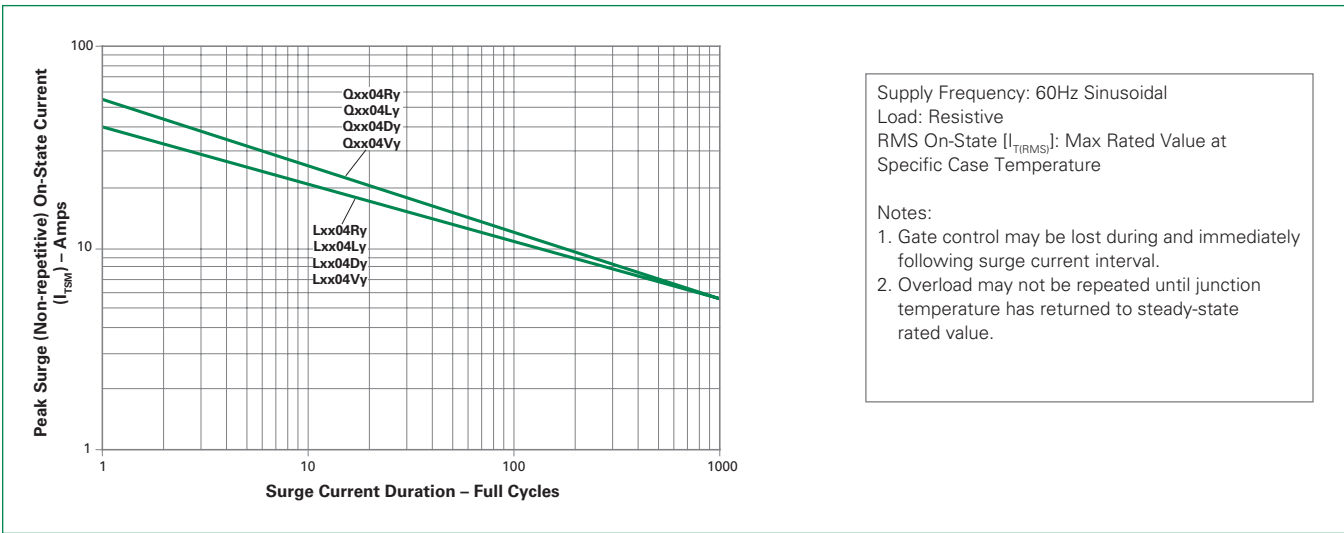


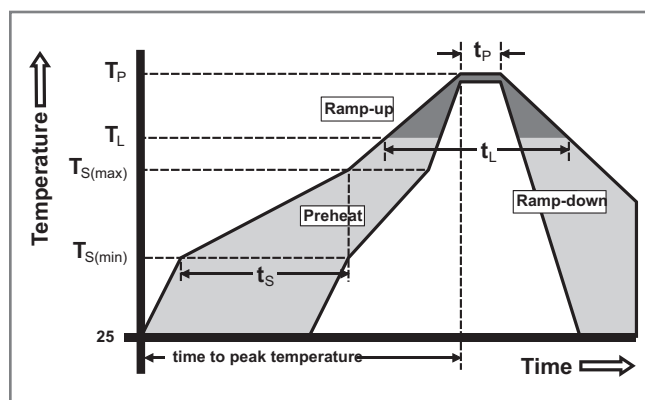
Figure 10: Surge Peak On-State Current vs. Number of Cycles



Note: xx = voltage, y = sensitivity

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260°C $+0/-5$
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability classification 94V-0
Terminal Material	Copper Alloy

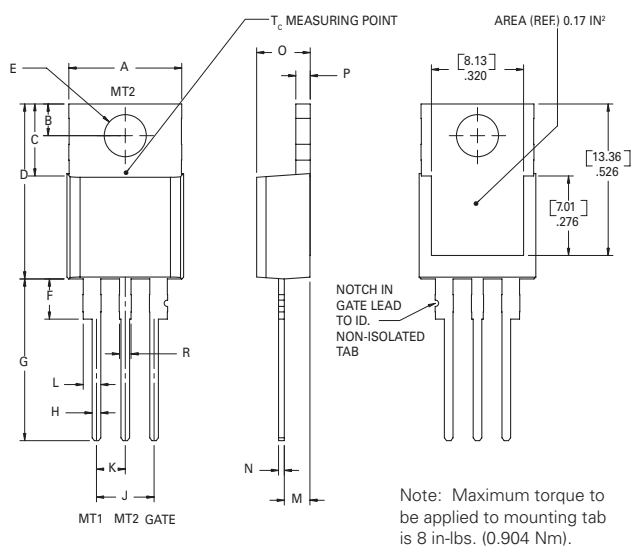
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

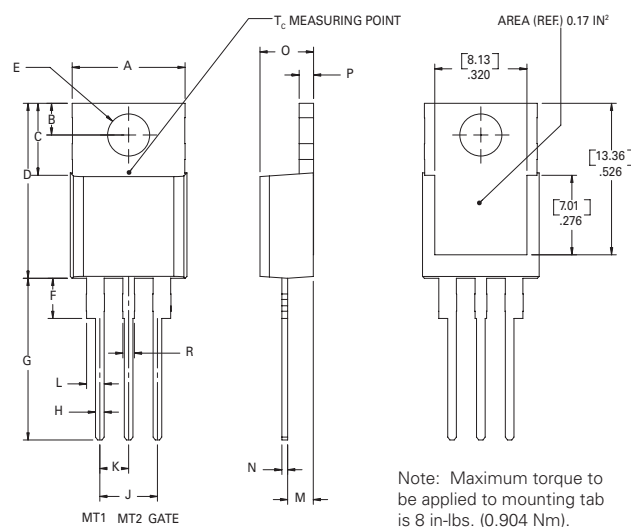
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Thermal Shock	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell time at each temperature; 10 sec (max) transfer time between temperature
Autoclave	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



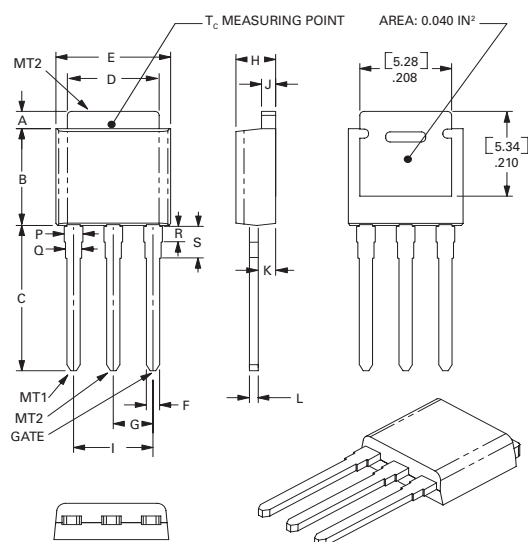
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



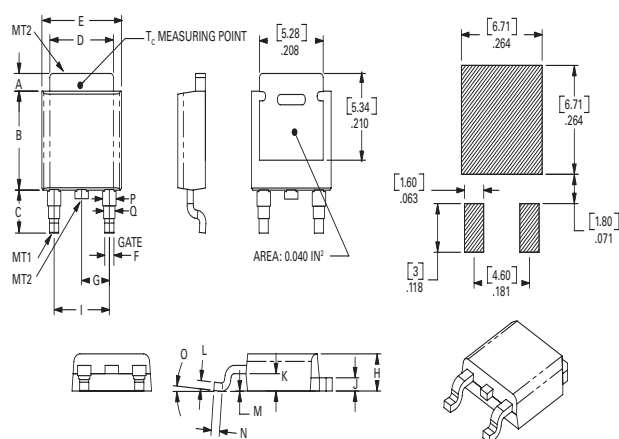
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-251AA (V-Package) — V-PAK Through Hole



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.044	0.050	1.02	1.11	1.27
B	0.235	0.242	0.245	5.97	6.15	6.22
C	0.350	0.361	0.375	8.89	9.18	9.53
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.66	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.34	2.41
I	0.176	0.180	0.184	4.47	4.57	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.01	1.12
L	0.018	0.020	0.023	0.46	0.52	0.58
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11
R	0.034	0.039	0.044	0.86	1.00	1.11
S	0.074	0.079	0.084	1.86	2.00	2.11

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.043	0.050	1.02	1.09	1.27
B	0.235	0.243	0.245	5.97	6.16	6.22
C	0.106	0.108	0.113	2.69	2.74	2.87
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.65	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.33	2.41
I	0.176	0.179	0.184	4.47	4.55	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.02	1.12
L	0.018	0.020	0.023	0.46	0.51	0.58
M	0.000	0.000	0.004	0.00	0.00	0.10
N	0.021	0.026	0.027	0.53	0.67	0.69
O	0°	0°	5°	0°	0°	5°
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11

Product Selector

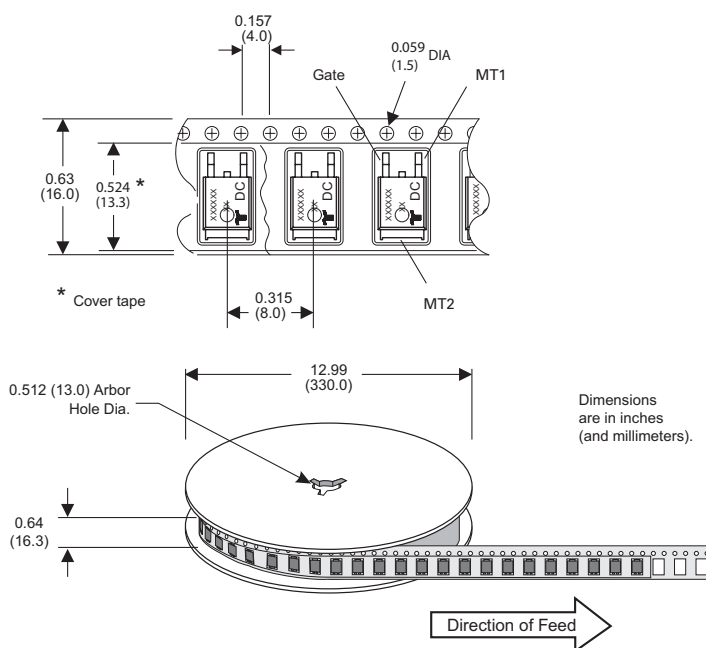
Part Number	Voltage				Gate Sensitivity Quadrants		Type	Package
	400V	600V	800V	1000V	I – II – III	IV		
Lxx04L3	X	X			3 mA	3 mA	Sensitive Triac	TO-220L
Lxx04D3	X	X			3 mA	3 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R3	X	X			3mA	3mA	Sensitive Triac	TO-220R
Lxx04V3	X	X			3 mA	3 mA	Sensitive Triac	TO-251 V-PAK
Lxx04L5	X	X			5 mA	5 mA	Sensitive Triac	TO-220L
Lxx04D5	X	X			5 mA	5 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R5	X	X			5mA	5mA	Sensitive Triac	TO-220R
Lxx04V5	X	X			5 mA	5 mA	Sensitive Triac	TO-251 V-PAK
Lxx04L6	X	X			5 mA	10 mA	Sensitive Triac	TO-220L
Lxx04D6	X	X			5 mA	10 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R6	X	X			5mA	10mA	Sensitive Triac	TO-220R
Lxx04V6	X	X			5 mA	10 mA	Sensitive Triac	TO-251 V-PAK
Lxx04L8	X	X			10 mA	20 mA	Sensitive Triac	TO-220L
Lxx04D8	X	X			10 mA	20 mA	Sensitive Triac	TO-252 D-PAK
Lxx04R8	X	X			10mA	20mA	Sensitive Triac	TO-220R
Lxx04V8	X	X			10 mA	20 mA	Sensitive Triac	TO-251 V-PAK
Qxx04L3	X	X			10 mA		Standard Triac	TO-220L
Qxx04D3	X	X			10 mA		Standard Triac	TO-252 D-PAK
Qxx04V3	X	X			10 mA		Standard Triac	TO-251 V-PAK
Qxx04R3	X	X			10mA		Standard Triac	TO-220R
Qxx04L4	X	X	X	X	25 mA		Standard Triac	TO-220L
Qxx04D4	X	X	X	X	25 mA		Standard Triac	TO-252 D-PAK
Qxx04R4	X	X	X	X	25mA		Standard Triac	TO-220R
Qxx04V4	X	X	X	X	25 mA		Standard Triac	TO-251 V-PAK

Packing Options

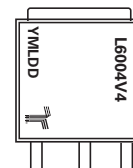
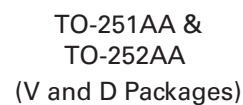
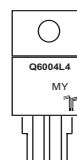
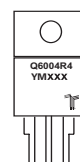
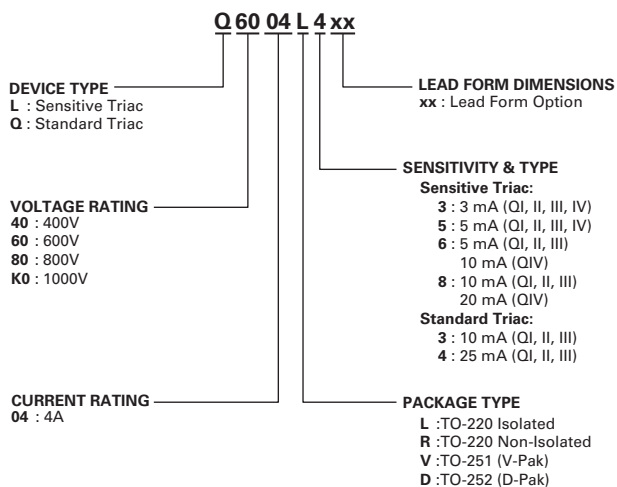
Part Number	Marking	Weight	Packing Mode	Base Quantity
L/Q004L/Ry/TP	L/Qxx04L/Ry	2.2 g	Bulk	500
L/Qxx04LyTP	L/Qxx04Ly	2.2 g	Tube	500 (50 per tube)
L/Qxx04DyRP	L/Qxx04Dy	0.3 g	Embossed Carrier	2500
L/Qxx04DyTP	L/Qxx04Dy	0.3 g	Tube Pack	750 (75 per tube)
L/Qxx04VyTP	L/Qxx04Vy	0.4 g	Tube Pack	750 (75 per tube)

Note: xx = Voltage; y = Sensitivity

Meets all EIA-481-2 Standards



Part Marking System





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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